

HUF76609D3S

HUF76609D3S Information

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For Reference Only		us Website: https://www.heisener.com E-mail: salesdept@heisener.com	Request a Quote

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HUF76609D3S Specifications

Manufacturer Part NumberHUF76609D3SManufacturerFairchild/ON SemiconductorCategoryDiscrete Semiconductor ProductsCategoryTransistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesUltraFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250µAInput Capacitance (Ciss) (Max) @ Vds425pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)49W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 10A, 10VOperating Temperature-55° c ~ 175°C (TJ)Mounting TypeSurface Mount			
CategoryDiscrete Semiconductor Products Transistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesUltraFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)45V, 10VVgs(th) (Max) @ Id3V @ 250µAGate Charge (Qg) (Max) @ Vds16nC @ 10VFET Feature-Power Dissipation (Max)49W (Tc)Rds On (Max) @ Id, Vgs160 mohm @ 10A, 10VRds On (Max) @ Id, Vgs55°C ~ 175°C (TJ)	Manufacturer Part Number	HUF76609D3S	
Transistors - FETs, MOSFETs - SinglePackageTO-252-3, DPak (2 Leads + Tab), SC-63SeriesUltraFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)100VCurrent - Continuous Drain (Id) @ 25°C10A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id3V @ 250µAGate Charge (Qg) (Max) @ Vds16nC @ 10VInput Capacitance (Ciss) (Max) @ Vds±16VVgs (Max)±16VFET Feature-Power Dissipation (Max)49W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)	Manufacturer	Fairchild/ON Semiconductor	
Package TO-252-3, DPak (2 Leads + Tab), SC-63 Series UltraFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vds 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 49W (Tc) Rds On (Max) @ Id, Vgs 160 mOhnm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Category	Discrete Semiconductor Products	
Series UltraFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 160 mOhm @ 10A, 10V Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V		Transistors - FETs, MOSFETs - Single	
FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 49W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Package	TO-252-3, DPak (2 Leads + Tab), SC-63	
Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 49W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Series	UltraFET?	
Drain to Source Voltage (Vdss) 100V Current - Continuous Drain (Id) @ 25°C 10A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 49W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	FET Type	N-Channel	
Current - Continuous Drain (Id) @ 25°С IOA (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 49W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Technology	MOSFET (Metal Oxide)	
Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 3V @ 250μA Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 9W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Drain to Source Voltage (Vdss)	100V	
Vgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs16nC @ 10VInput Capacitance (Ciss) (Max) @ Vds425pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)49W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)	Current - Continuous Drain (Id) @ 25°C	10A (Tc)	
Gate Charge (Qg) (Max) @ Vgs 16nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 49W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V	
Input Capacitance (Ciss) (Max) @ Vds 425pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 49W (Tc) Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	Vgs(th) (Max) @ Id	3V @ 250µA	
Vgs (Max)±16VFET Feature-Power Dissipation (Max)49W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)	Gate Charge (Qg) (Max) @ Vgs	16nC @ 10V	
FET Feature-Power Dissipation (Max)49W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	425pF @ 25V	
Power Dissipation (Max)49W (Tc)Rds On (Max) @ Id, Vgs160 mOhm @ 10A, 10VOperating Temperature-55°C ~ 175°C (TJ)	Vgs (Max)	±16V	
Rds On (Max) @ Id, Vgs 160 mOhm @ 10A, 10V Operating Temperature -55°C ~ 175°C (TJ)	FET Feature	-	
Operating Temperature $-55^{\circ}\text{C} \sim 175^{\circ}\text{C} \text{(TJ)}$	Power Dissipation (Max)	49W (Tc)	
	Rds On (Max) @ Id, Vgs	160 mOhm @ 10A, 10V	
Mounting Type Surface Mount	Operating Temperature	-55°C ~ 175°C (TJ)	
	Mounting Type	Surface Mount	
Supplier Device Package D-Pak	Supplier Device Package	D-Pak	
Package / Case TO-252-3, DPak (2 Leads + Tab), SC-63	Package / Case	TO-252-3, DPak (2 Leads + Tab), SC-63	
Report errors?		Report errors?	

HUF76609D3S Guarantees



Quality Guarantees

We provide 90 days warranty. * If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.

SERVICE SUARANTEE

Service Guarantees

We guarantee 100% customer satisfaction. Our experienced sales team and tech support team back our services to satisfy all our customers.

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HUF76609D3S Shipping Methods



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